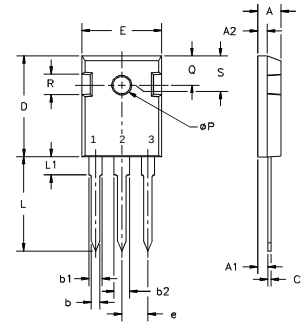


Symbol	Test Conditions	Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = -10\text{ V}; I_D = I_{D25}$, pulse test	5	9	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$		4700	pF
C_{oss}			430	pF
C_{rss}			135	pF
$t_{d(on)}$	$V_{GS} = -10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 4.7\ \Omega$ (External)		33	ns
t_r			27	ns
$t_{d(off)}$			35	ns
t_f			35	ns
$Q_{g(on)}$	$V_{GS} = -10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		160	nC
Q_{gs}			46	nC
Q_{gd}			92	nC
R_{thJC}			0.42	K/W
R_{thCS}		0.25		K/W

Source-Drain Diode		Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_s	$V_{GS} = 0$	10P50 11P50		-10 A -11 A
I_{SM}	Repetitive; pulse width limited by T_{JM}	10P50 11P50		-40 A -44 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			-3 V
t_{rr}	$I_F = I_S, di/dt = 100\text{ A}/\mu\text{s}$		500	ns

TO-247 AD Outline


Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC